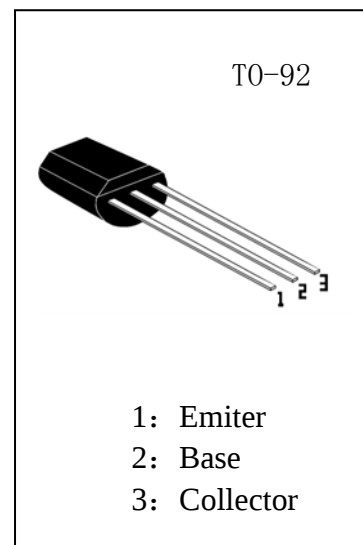


低压晶体管

- 集电极电流 $I_c = -500\text{mA}$
- 高耗散功率 $P_c = 625\text{mW}$
- 与 S8050 对管

极限参数(Absolute Maximum Ratings) $T_a = 25^\circ\text{C}$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cb0}	-40	V
Collector-Emitter Voltage	V_{ce0}	-25	V
Emitter-Base Voltage	V_{eb0}	-5	V
Collector Current	I_c	-500	mA
Collector Dissipation	P_c	625	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$


电性能(Electrical Characteristic) $T_a = 25^\circ\text{C}$

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BV_{cb0}	Collector-Base Breakdown Voltage	$I_c = -100\mu\text{A}$ $I_e = 0$	-40			V
BV_{ce0}	Collector-Emitter Breakdown Voltage	$I_c = -1\text{mA}$ $I_b = 0$	-25			V
BV_{eb0}	Emitter-Base Breakdown Voltage	$I_e = -100\mu\text{A}$ $I_c = 0$	-5			V
I_{c0}	Collector Cutoff Current	$V_{cb} = -25\text{V}$, $I_e = 0$			-100	nA
I_{e0}	Emitter Cutoff Current	$V_{eb} = -3\text{V}$, $I_c = 0$			-100	nA
I_{ce0}	Collector Cutoff Current	$V_{ce} = -20\text{V}$, $I_b = 0$			-10	μA
$V_{ce(sat)}$	Collector-Emitter Saturation Voltage	$I_c = -500\text{mA}$, $I_b = -50\text{mA}$		-0.26	-0.6	V
$V_{be(sat)}$	Base-Emitter Saturation Voltage	$I_c = -500\text{mA}$, $I_b = -50\text{mA}$		-0.98	-1.2	V
$V_{be(on)}$	Base-Emitter On Voltage	$V_{ce} = -1\text{V}$, $I_c = -10\text{mA}$	-0.6	-0.67	-0.7	V
H_{fe1}	DC Current Gain	$V_{ce} = -1\text{V}$, $I_c = -50\text{mA}$	120		500	
H_{fe2}	DC Current Gain	$V_{ce} = -1\text{V}$, $I_c = -500\text{mA}$	30			

CLASS	C	D				
Hfe1	120-200	200-250	250-300	200-300	300-400	400-500